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ICSCRM 2005

International Conference on Silicon Carbide and Related Materials

September 18–23, 2005

Pittsburgh, Pennsylvania, USA

First Call For Papers



ICSCRM 2005

Semiconductor materials science and technology have provided a solid foundation for the remarkable performance of current electronic and optical device technology. Wide bandgap semiconductors—typically defined as materials exhibiting an electronic bandgap greater than 2.0 eV—are emerging as materials capable of driving continued device performance enhancements for many years to come. Silicon Carbide (SiC) has been studied for decades, but recent development has firmly established commercial products in optical, RF and power components. Continued research in the field will assure that the rapid developmental timeline for SiC-based device technology can continue into the future.

The International Conference on Silicon Carbide and Related Materials (ICSCRM '05) will be held September 18-23, 2005, at the Westin Hotel and Convention Center, in Pittsburgh, Pennsylvania (USA). This conference has become the pre-eminent forum to discuss new research results, and assess the true “state of the art” for SiC, as well as gallium nitride (GaN) and other related wide bandgap semiconductors – spanning the entire spectrum from fundamental science of materials through device performance. Abstracts are solicited in the following broad topic areas: Materials Growth (Bulk and Epitaxial), Materials Characterization and Theory, Device Processing and Device Optimization/Performance.

Abstract Instructions:

One short abstract (200 words maximum) should be provided for inclusion in the conference program book. A second “Extended” abstract should be provided. The abstract must be prepared as a Microsoft Word, or .pdf file. The abstract should be written in English. Abstract format is Times, 12 point font. This abstract can be a maximum of two (2) pages, including figures and tables, with 2.5cm margins on all four sides. All figures, including captions, should be on the last page. **Figures should be saved as .bmp, .gif, .jpeg, .pict, or .tiff, and inserted into the abstract.** The abstract should be headed by the title, author(s), affiliation(s), address(es). The name of the corresponding author should be underlined, and the abstract should contain contact information for the corresponding author (telephone number, fax number and e-mail address).

Abstract Deadline: March 15, 2005

Prospective authors should submit abstracts electronically to the TMS Conference Management System (CMS) using the following site: <http://cms.tms.org>. Follow the instructions to access the year “2005” and the “11th International Conference on Silicon Carbide and Related Materials”.

Please contact the Programming Services Department at TMS for assistance or further instruction.

TMS Technical Programming Department
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